

Form PTO-1449 (REV. 8-83) US Dept. of Commerce PATENT & TRADEMARK OFFICE INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)			ATTY DOCKET NO. 118211		APPLICATION NO. New U.S. Patent Application 10/765,197	
			APPLICANT Mutsumi KIMURA			
			FILING DATE January 28, 2004		Group 2822	
U.S. PATENT DOCUMENTS						
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS
<hr/> <hr/> <hr/>						
FOREIGN PATENT DOCUMENTS						
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB CLASS
<i>ms</i>	1	JP A 2001-282424 w/ abst & trans	10/12/2001	Japan		
	2	JP A 2001-282423 w/ abst & trans	10/12/2001	Japan		
	3	JP A 2003-133708 w/ abst & trans	05/09/2003	Japan		
	4	JP A 2003-77940 w/ abst & trans	03/14/2003	Japan		
	5	JP A 2002-368282 w/ abst & trans	12/20/2002	Japan		
	6	JP A 2002-343944 w/ abst & trans	11/29/2002	Japan		
	7	JP A 2002-314123 w/ abst & trans	10/25/2002	Japan		
	8	JP A 2002-314052 w/ abst & trans	10/25/2002	Japan		
	9	JP A 2002-311858 w/ abst & trans	10/25/2002	Japan		
<i>ms</i>	10	JP A 2003-258210 w/ abst & trans	09/12/2003	Japan		
<hr/> <hr/> <hr/>						
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)						
<hr/> <hr/> <hr/> <hr/> <hr/>						
EXAMINER <i>John M. Soward</i>					DATE CONSIDERED <i>ims</i>	
Examiner: Initial if citation considered, whether or not citation is in conformance with M.P.E.P. 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.						

Date: January 28, 2004



Sheet 1 of 1

Form PTO-1449 (REV. 8-83)		US Dept. of Commerce PATENT & TRADEMARK OFFICE	ATTY DOCKET NO. 118211	APPLICATION NO. 10/765,197	
INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)		APPLICANT(S) Mutsumi KIMURA			
		FILING DATE January 28, 2004	GROUP 2822		
U.S. PATENT DOCUMENTS					
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS
FOREIGN PATENT DOCUMENTS					
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)					
<i>SH</i>	1	SHIMODA et al., "Surface Free Technology by Laser Annealing (SUFTLA)", <i>IEEE</i> , 1999, pp. 289-292.			
	2	UTSUNOMIYA et al., "Low Temperature Poly-Si TFTs on Plastic Substrate Using Surface Free Technology by Laser Ablation/Annealing (SUFTLA™)", <i>SID 00 DIGEST</i> , 2000, pp. 916-919.			
	3	SHIMODA, "Future Trend of TFTs", <i>Asia Display/IDW '01</i> , pp. 327-330.			
<i>SH</i>	4	UTSUNOMIYA et al., "Low Temperature Poly-Si TFT-LCD Transferred onto Plastic Substrate Using Surface Free Technology by Laser Ablation/Annealing (SUFTLA®)", <i>Asia Display/IDW '01</i> , pp. 339-342.			
EXAMINER	<i>John M. Smith</i>			DATE CONSIDERED	<i>5-1-05</i>
Examiner:	Initial if citation considered, whether or not citation is in conformance with M.P.E.P. 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.				

Date: February 17, 2004